

1-Line Bidirectional ESD Protection Diode



General description

Femtofarad bidirectional ElectroStatic Discharge (ESD) protection diode in a leadless ultra small DFN1006 Surface-Mounted Device (SMD) plastic package designed to protect one signal line from the damage caused by ESD and other transients. The combination of extremely low capacitance, high ESD maximum rating and ultra small package makes the device ideal for high-speed data line protection and antenna protection applications.

Features and benefits

- Bidirectional ESD protection of one line
- Femtofarad capacitance: $C_j = 0.35\text{pF}$ (Typ)
- Ultra low leakage current: nA Level
- Response time is typically $< 1\text{ ns}$
- IEC 61000-4-2; level 4 (ESD)

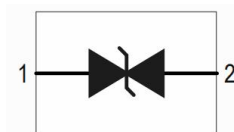
Application information

- USB3.0
- SATA and eSATA
- High- speed data lines
- HDMI
- Cellular handsets and accessories
- 10/100/1000 Mbit/s Ethernet
- Communication systems
- Computers and peripherals
- Portable electronics
- Antenna protection

Ordering information

Device	Package	Marking	Packaging
SLESD8LL5.0C	DFN1006-2L	21	10000/Tape & Reel

Schematic & Pin configuration

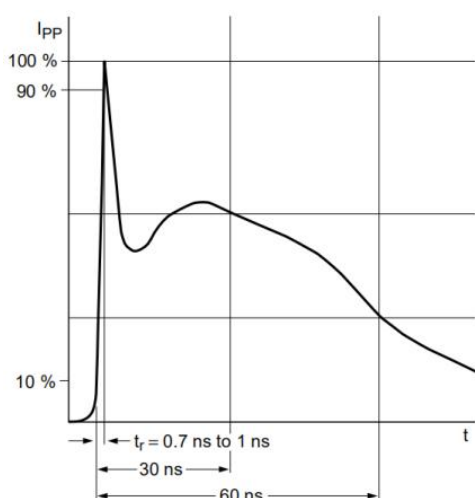
Simplified outline	Graphic symbol
	

Maximum Ratings ($T_{OP} = 25^{\circ}\text{C}$, unless otherwise specified)

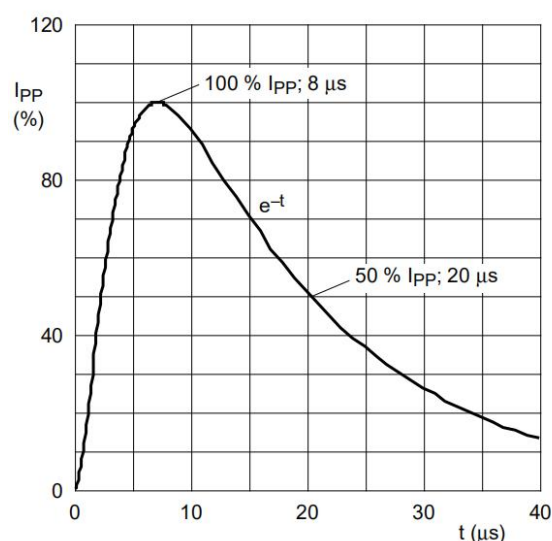
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_p = 8/20 \mu\text{s}$)	P_{PPM}	72	W
Rated Peak Pulse Current ($T_p = 8/20 \mu\text{s}$)	I_{PPM}	4	A
Maximum lead temperature for soldering during 10s	T_L	260	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Operating Temperature Range	T_{OP}	-40 to +125	$^{\circ}\text{C}$
Maximum junction temperature	T_j	150	$^{\circ}\text{C}$
ESD voltage IEC 61000-4-2 (air discharge)	V_{ESD}	25	kV
ESD voltage IEC 61000-4-2 (contact discharge)	V_{ESD}	25	kV

Electrical Characteristics ($T_{OP} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Reverse Working Voltage	V_{RWM}	--	--	5.0	V	
Breakdown Voltage	V_{BR}	6.5	--	9.0	V	$I_T=1\text{mA}$
Leakage Current I_{Leak}	I_R	--	--	100	nA	$V_{RWM}=5\text{V}$
Clamping Voltage	V_C	--	16.0	18.0	V	$I_{PP}=4\text{A}, T_p=8/20\mu\text{s}$
Junction Capacitance	C_j	--	0.35	0.40	pF	$V_R=0\text{V}, f=1\text{MHz}$



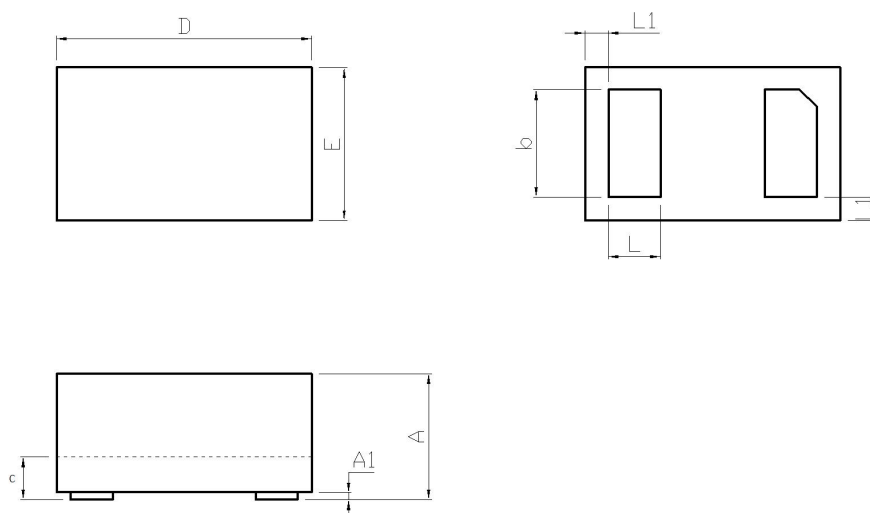
IEC61000-4-2 Waveform



IEC 61000-4-5 Waveform(8/20μs pulse)

Package Outline Dimensions

DFN1006-2L



DFN1006-2L (mm)			
Dim	Min	Typ.	Max
A	0.40	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.5	0.55
c	0.1	0.12	0.14
D	0.95	1.00	1.05
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.035	0.05	0.065
h	0.07	0.12	0.17